

Data Provided: useful definitions and equations at end of paper (after Q4)

DEPARTMENT OF ELECTRONIC AND ELECTRICAL ENGINEERING

Autumn Semester 2009 - 2010 (2 hours)

ELECTRONIC DEVICES IN CIRCUITS 2

Answer THREE questions. No marks will be awarded for solutions to a fourth question. Solutions will be considered in the order in which they are presented in the answer book. Trial answers will be ignored if they are clearly crossed out. The numbers given after each section of a question indicate the relative weighting of that section.

- 1 (a) (i) Write down the high frequency and low frequency gains of the circuit of figure 1 in terms of the circuit components. {2}
 - (ii) Show that the transfer function, v_0/v_i of the circuit is given by:

$$\frac{v_o}{v_i} = k \frac{\left(1 + j \frac{f}{f_1}\right)}{\left(1 + j \frac{f}{f_0}\right)}, \text{ where } k = 1, f_0 = \frac{1}{2\pi C_1 (R_1 + R_2)} \text{ and } f_1 = \frac{1}{2\pi C_1 R_2}$$
 {3}

(iii) If $R_1 = R_2 = 10 \text{k}\Omega$ and $C_1 = 10 \text{n}$ F, sketch the response you would expect to observe in response to an ideal 10V step input occurring at t = 0. Label the starting and aiming voltages of the response shape and evaluate its time constant. $\{5\}$

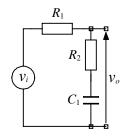


Figure 1

- (b) An op-amp with a gain-bandwidth product of 20MHz is connected as a non-inverting amplifier with a gain of 50.
 - (i) What is the -3dB bandwidth of the amplifier and its associated time constant? {2}
 - (ii) What is |gain| and the phase of the output signal with respect to the input signal at a frequency of 1MHz? {5}
 - (iii) If the amplifier has a slew rate of $70V \,\mu s^{-1}$, what is the maximum frequency of 10V peak symmetrical triangular waveform that the amplifier can support at its output? $\{3\}$

- 2 (i) Briefly describe, with the aid of sketches if appropriate, the main features of Butterworth and Chebychev low-pass filter amplitude responses. Point out two main differences between Butterworth and Chebychev low-pass filter behaviour, one in the pass-band and one in the cut-off region of their responses. What makes the Butterwoth response attractive from a practical point of view? {5}
 - (ii) Draw a circuit diagram to show how a second order, low-pass Sallen and Key circuit can be realised using an operational amplifier, two resistors and two capacitors. (no other components may be used.) {3}
 - (iii) The transfer function of the second order, low-pass Sallen and Key circuit of part (ii), made with equal resistor values, is

$$\frac{v_o}{v_i} = \frac{1}{1 + s \, 2C_2 R + s^2 C_1 C_2 R^2} \,.$$

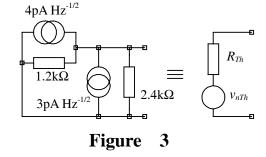
Find expressions for the undamped natural frequency, ω_n , and quality factor, q, of the circuit. $\{3\}$

(iv) A third order, 3dB ripple, Chebychev low-pass filter with a cut-off frequency of 20kHz is required for a particular application. The frequency normalised transfer function of the required filter is

$$\frac{v_o}{v_i} = \frac{1}{(s^2 + 0.299s + 0.839)(s + 0.299)}.$$

Rearrange the factors into standard forms and hence identify the q and ω_n required for the second order factor and the time constant required for the first order factor. $\{7\}$

- (v) If the second order factor of part (iv) is to be realised using the Sallen and Key transfer function of part (iii), what ratio of C_1 to C_2 is necessary? {2}
- 3 (a) Figure 3 shows a network consisting of noisy resistors and noise sources.
 - (i) Find the noise free resistance R_{Th} and the root mean square noise voltage v_{nTh} (in terms of V Hz^{-1/2}) which form the Thevenin equivalent of the noisy network. $\{8\}$
 - (ii) If all of v_{nTh} is considered as originating in R_{Th} , what is the noise temperature of R_{Th} ? {2}



(b) Derive an expression for noise factor, F, in terms of N_I , N_A and A_P , the input and added noise powers and the amplifier power gain respectively. Briefly justify key steps in your derivation. $\{4\}$ Q3 continued overleaf

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Q3 CONTINUED ...

- (c) A particular amplifier has equivalent input noise voltage and current generators of 12nV Hz^{-1/2} and 2pA Hz^{-1/2} respectively. The amplifier has a voltage gain of 50 and its output is passed through a filter with a noise bandwidth of 20kHz. What is the signal to noise ratio at the filter output when the input signal is a $30\mu\text{V}$ rms sinusoidal source that has a noisy Thevenin resistance of $10\text{k}\Omega$. Assume that the temperature is 300K, that the filter generates no noise and that the frequency of the sinusoid lies within the filter bandwidth. $\{6\}$
- 4 (a) Figure 4 shows the output and output biasing stages typically found in operational amplifiers and power amplifiers. The voltages $+V_S$ and $-V_S$ are measured with respect to ground and V_I is has a dc component appropriate to make the dc component of V_O equal to zero.
 - (i) Briefly explain the reason for the inclusion of T_1 , R_1 and R_2 between the two output transistor bases. {2}
 - (ii) Why do designers aim to ensure that a small but finite current flows through the output transistors, T_2 and T_3 , when the output signal current is zero? {2}
 - (iii) What two purposes are satisfied by R_3 and R_4 ? {2}

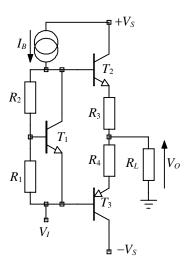


Figure 4

(b) (i) Show that the maximum power dissipated within each output device in a class B amplifier, such as that in figure 4, is given by

$$P_{DMAX} = \frac{V_S^2}{\pi^2 R_L} \quad \{5\}$$

A particular class B amplifier is designed to deliver power to a 4Ω resistive load. If the power supply voltage, $V_S = 40$ V, the peak load voltage can reach V_S and the signal waveshape is sinusoidal,

- (ii) What is the maximum power that could be delivered to the 4Ω resistive load if the load voltage waveform must remain sinusoidal? $\{I\}$
- (iii) Sketch the waveshape of the current that you would expect to be drawn from the positive power supply for the conditions of part (b) (ii). What is the peak value of this supply current waveform? {3}
- (iv) Both output devices are mounted on a single heatsink but are electrically insulated from it by mica washers with a thermal resistance of 1°C W⁻¹. The maximum junction temperature of the transistors is specified as 150°C and their junction to case thermal resistance is 0.75°C W⁻¹. The ambient temperature may reach 35°C and the heatsink temperature must not exceed 85°C. What is the maximum heatsink thermal resistance that can be used if neither of the limiting temperature conditions is to be violated? {5}

You may find some of the following relationships and definitions useful:

$$I = C \frac{dV}{dt}$$
 $\omega = 2\pi f$ $V(t) = (V_{START} - V_{FINISH}) \exp\left(\frac{-t}{\tau}\right) + V_{FINISH}$

$$V_{AVE} = \frac{V_P}{\pi}$$
 for a half wave rectified sinusoid $V_{rms} = \frac{V_P}{\sqrt{2}}$ for a sinusoid

$$V_{AVE} = \frac{V_P}{4}$$
 for a half wave rectified triangular wave $V_{rms} = \frac{V_P}{\sqrt{3}}$ for a triangular wave

$$V_{AVE} = \frac{V_P}{2}$$
 for a half wave rectified square wave $V_{rms} = V_P$ for a square wave

$$v_o = A_v (v^+ - v^-)$$
 $A_v = \frac{A_0}{1 + s \tau_0} = \frac{A_0}{1 + j \frac{\omega}{\omega_0}}$ $\overline{v_n^2} = 4kTR \ V^2 \ Hz^{-1}$
 $\overline{t_n^2} = 2eI \ A^2 \ Hz^{-1}$ $\overline{v_n^2} = \frac{kT}{C} \ V^2$ $e = \text{electronic charge} = 1.602 \times 10^{-19} \ \text{C}$
 $k = \text{Boltzmann's constant} = 1.38 \times 10^{-23} \ \text{J K}^{-1}$ Room temperature = 300 K

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$$k = \text{Boltzmann's constant} = 1.38 \times 10^{-23} \text{ J K}^{-1}$$
 Room temperature = 300 K

Second order standard forms are:

$$\frac{v_o}{v_i} = k \frac{1}{\left(1 + \frac{s}{\omega_n q} + \frac{s^2}{\omega_n^2}\right)} \qquad \frac{\frac{s}{\omega_n q}}{\left(1 + \frac{s}{\omega_n q} + \frac{s^2}{\omega_n^2}\right)} \qquad \frac{\frac{s^2}{\omega_n^2}}{\left(1 + \frac{s}{\omega_n q} + \frac{s^2}{\omega_n^2}\right)} \qquad \frac{v_o}{v_i} = k \frac{\frac{s^2}{\omega_n^2}}{\left(1 + \frac{s}{\omega_n q} + \frac{s^2}{\omega_n^2}\right)}$$

gain in dB = $20\log \left| \frac{v_o}{v_i} \right|$ for voltage ratios and $10\log \left| \frac{P_o}{P_i} \right|$ for power ratios.

unit multipliers:
$$p = x10^{-12}$$
, $n = x10^{-9}$, $\mu = x10^{-6}$, $m = x10^{-3}$, $k = x10^{3}$, $M = x10^{6}$ $G = x10^{9}$

All the symbols have their usual meanings

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